

1           1.    A method comprising:  
2                modifying the viscosity of a wet etchant; and  
3                applying said etchant to a semiconductor layer.

1           2.    The method of claim 1 including increasing the  
2 viscosity of the etchant.

1           3.    The method of claim 2 where increasing the  
2 viscosity of a wet etchant includes adding a thickening  
3 agent to said wet etchant.

1           4.    The method of claim 2 where increasing the  
2 viscosity of a wet etchant includes dehydrating said wet  
3 etchant.

1           5.    The method of claim 2 including forming a mask  
2 over a layer to be etched and applying said wet etchant  
3 through said mask to the layer to be etched.

1           6.    The method of claim 5 including dipping a  
2 semiconductor wafer in a bath of said etchant of increased  
3 viscosity.

1           7.    The method of claim 2 including forming a stack  
2   on a semiconductor wafer including a metal layer to be  
3   etched, forming a mask over said metal layer, and etching  
4   said metal layer with said increased viscosity etchant.

1           8.    A method comprising:  
2                    increasing the viscosity of a wet etchant to  
3   reduce the amount of undercutting of an etched layer.

1           9.    The method of claim 8 including increasing the  
2   viscosity of a wet etchant by dehydrating the etchant.

1           10.   The method of claim 8 including increasing the  
2   viscosity of the etchant by adding a thickening agent to  
3   said etchant.

1           11.   The method of claim 8 including applying said  
2   increased viscosity wet etchant to a semiconductor wafer to  
3   etch a layer on said wafer.

1           12.   A wet etchant comprising:  
2                    a material to etch a semiconductor layer; and  
3                    a thickening agent.

1           13.   The etchant of claim 12 wherein said thickening  
2   agent is glycol.

1           14. The etchant of claim 12 wherein said thickening  
2 agent is glycerol.

1           15. The etchant of claim 12 wherein said etchant is  
2 sulfuric acid.

1           16. A wet etchant comprising:  
2               a dehydrated etching material.

1           17. The etchant of claim 16 wherein said material is  
2 sulfuric acid.

1           18. A wet etchant comprising:  
2               a material to etch a semiconductor layer, said  
3 material having a viscosity of greater than one centipoise.

1           19. The etchant of claim 18 wherein said etchant is  
2 dehydrated.

1           20. The etchant of claim 18 including a thickening  
2 agent.

1           21. The etchant of claim 18 including sulfuric acid.